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Texas Instruments
CSD16412Q5A

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Datasheet of CSD16412Q5A - MOSFET N-CH 25V 52A 8-SON
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CSD16412Q5A

N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16412Q5A

FEATURES

- **Ultra Low Qg and Qgd**
- **Low Thermal Resistance**
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- **SON 5mm x 6mm Plastic Package**

APPLICATIONS

- **Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems**
- **Optimized for Control FET Applications**

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.

PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	25		V
Q_g	Gate Charge Total (4.5V)	2.9		nC
Q_{gd}	Gate Charge Gate to Drain	0.7		nC
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 4.5V	13	mΩ
		V_{GS} = 10V	9	mΩ
$V_{GS(th)}$	Threshold Voltage	2		V

ORDERING INFORMATION

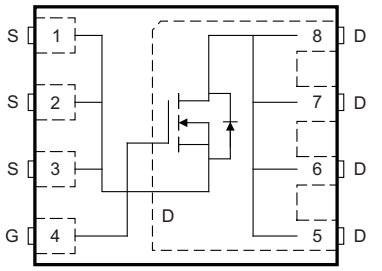
Device	Package	Media	Qty	Ship
CSD16412Q5A	SON 5 × 6 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

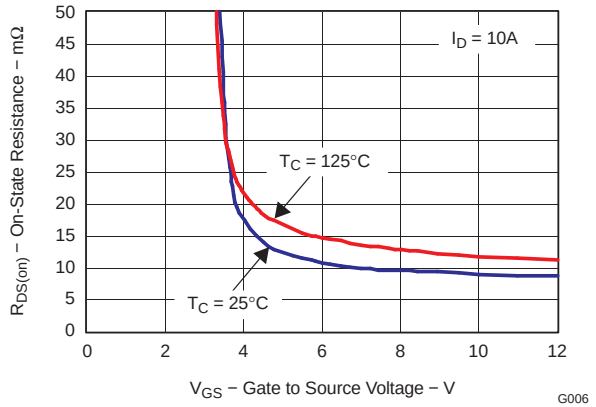
T_A = 25°C unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+16 / –12	V
I_D	Continuous Drain Current, T_C = 25°C	52	A
	Continuous Drain Current(1)	14	A
I_{DM}	Pulsed Drain Current, T_A = 25°C(2)	91	A
P_D	Power Dissipation(1)	3	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, single pulse I_D = 17A, L = 0.1mH, R_G = 25Ω	14	mJ

(1) $R_{\theta JA}$ = 42°C/W on 1in² Cu (2 oz) on 0.060" thick FR4 PCB.
(2) Pulse width ≤300μs, duty cycle ≤2%

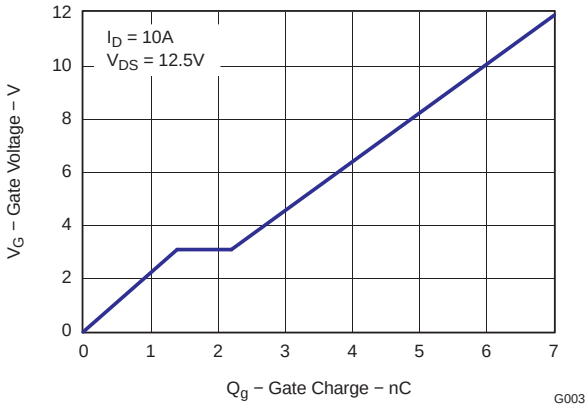
Top View



$R_{DS(ON)}$ vs V_{GS}



Gate Charge



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ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_D = 250µA	25			V
I_{DSS}	Drain to Source Leakage Current	V_{GS} = 0V, V_{DS} = 20V			1	µA
I_{GSS}	Gate to Source Leakage Current	V_{DS} = 0V, V_{GS} = +16/-12V			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	1.7	2.0	2.3	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 4.5V, I_D = 10A		13	16	mΩ
		V_{GS} = 10V, I_D = 10A		9	11	mΩ
g_{fs}	Transconductance	V_{DS} = 15V, I_D = 10A		33		S
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{GS} = 0V, V_{DS} = 12.5V, f = 1MHz		410	530	pF
C_{OSS}	Output Capacitance			350	450	pF
C_{RSS}	Reverse Transfer Capacitance			32	42	pF
R_g	Series Gate Resistance			0.7	1.4	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 12.5V, I_D = 10A		2.9	3.8	nC
Q_{gd}	Gate Charge Gate to Drain			0.7		nC
Q_{gs}	Gate Charge Gate to Source			1.4		nC
Qg(th)	Gate Charge at Vth			0.9		nC
Q_{OSS}	Output Charge	V_{DS} = 13V, V_{GS} = 0V		7		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 12.5V, V_{GS} = 4.5V, I_D = 10A R_G = 2Ω		5.5		ns
t_r	Rise Time			7.1		ns
$t_{d(off)}$	Turn Off Delay Time			5.7		ns
t_f	Fall Time			3.3		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_S = 10A, V_{GS} = 0V		0.85	1.0	V
Q_{rr}	Reverse Recovery Charge	V_{dd}= 13V, I_F = 10A, di/dt = 300A/µs		12		nC
t_{rr}	Reverse Recovery Time	V_{dd}= 13V, I_F = 10A, di/dt = 300A/µs		16		ns

THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case(1)			3.7	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient(1) (2)			53	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 × 1.5 in 0.060 inch thick FR4 board. $R_{\theta JC}$ is specified by design while $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 Material with 1 $inch^2$ of 2 oz. Cu.

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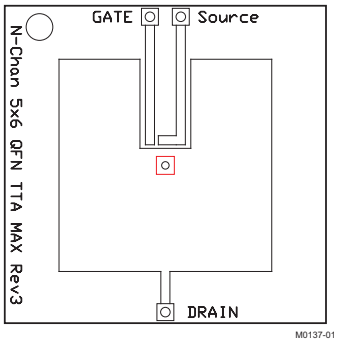
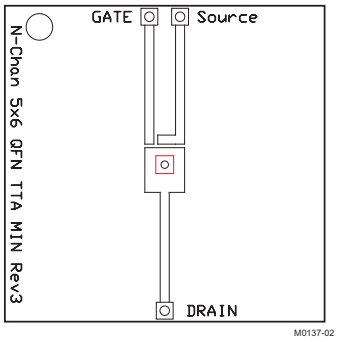


Max $R_{\theta JA}$ = 53°C/W when mounted on 1inch^2 of 2 oz. Cu.



Max $R_{\theta JA}$ = 119°C/W when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

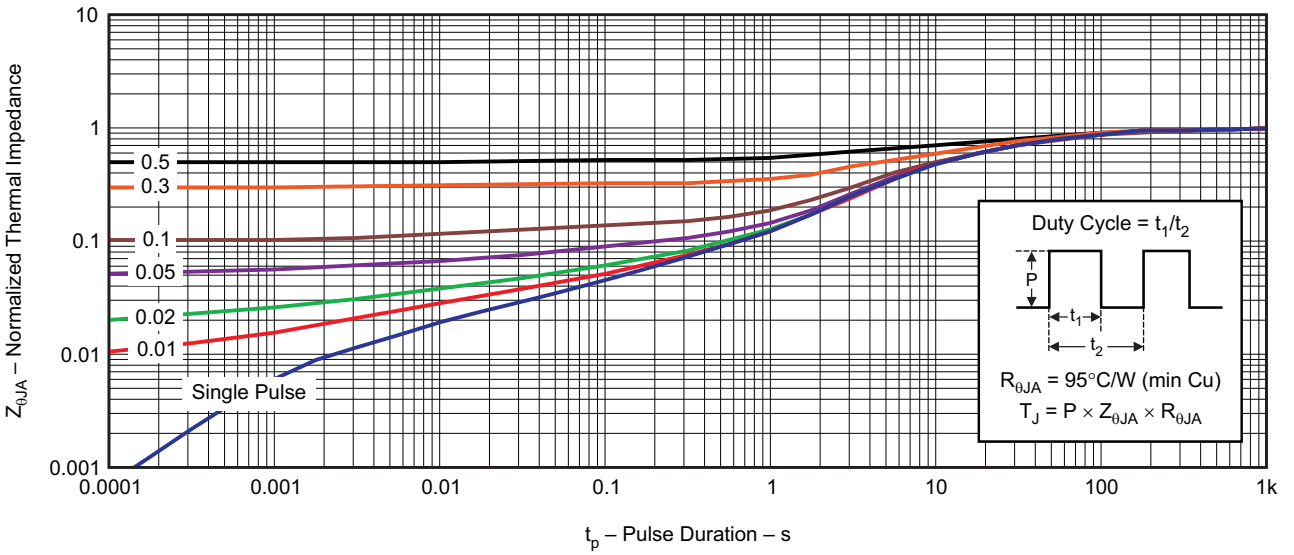


Figure 1. Transient Thermal Impedance

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TYPICAL MOSFET CHARACTERISTICS (continued)

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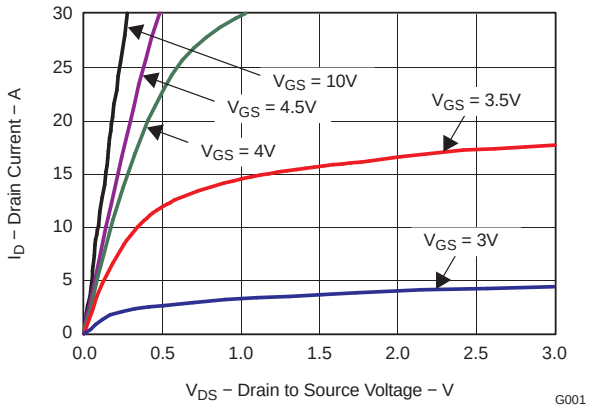

Figure 2. Saturation Characteristics

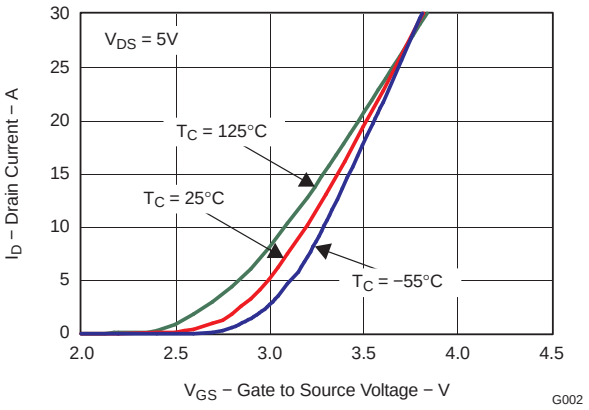

Figure 3. Transfer Characteristics

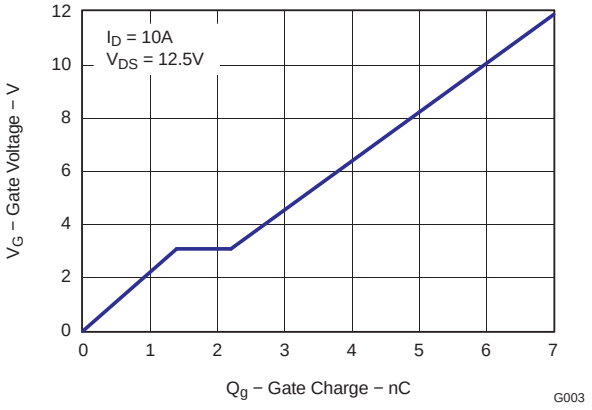

Figure 4. Gate Charge

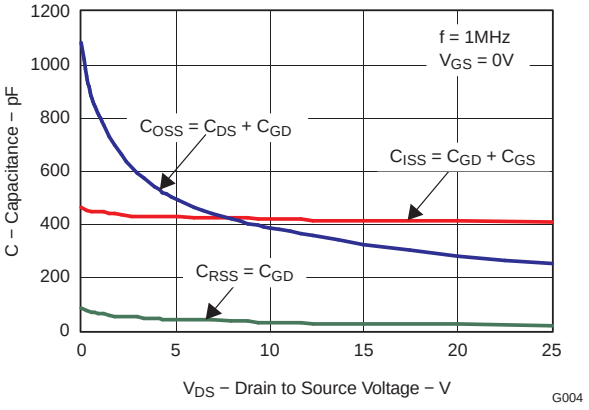

Figure 5. Capacitance

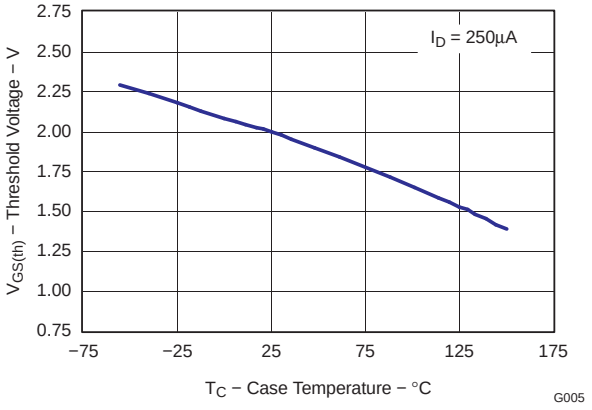

Figure 6. Threshold Voltage vs. Temperature

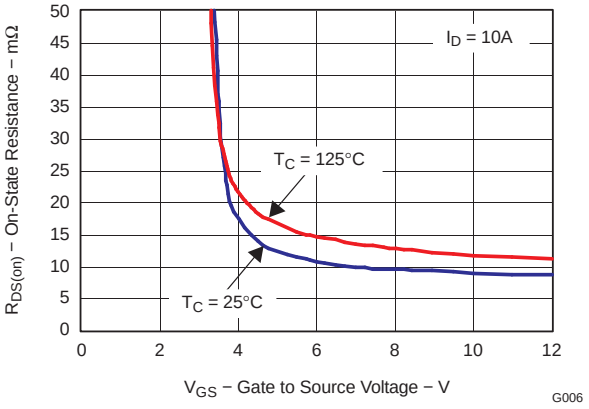

Figure 7. On Resistance vs. Gate Voltage

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TYPICAL MOSFET CHARACTERISTICS (continued)

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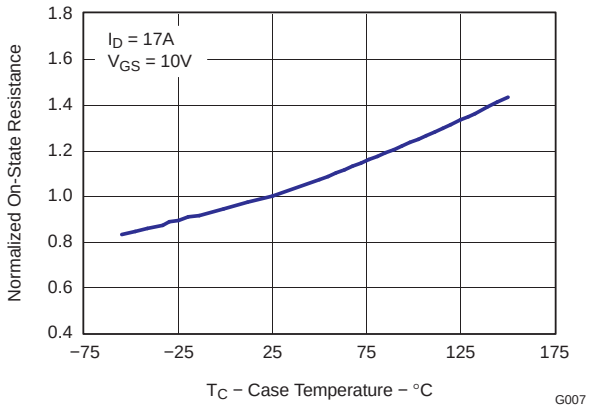

Figure 8. On Resistance vs. Temperature

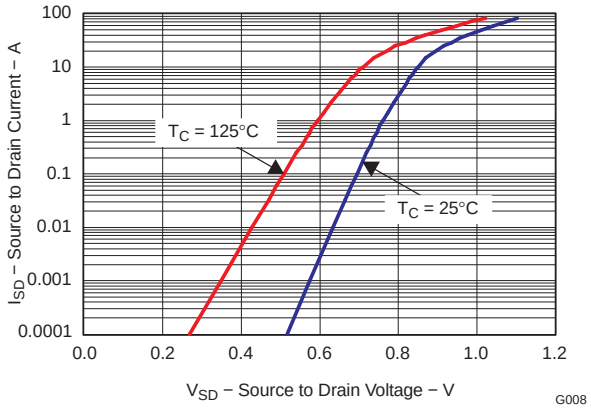

Figure 9. Typical Diode Forward Voltage

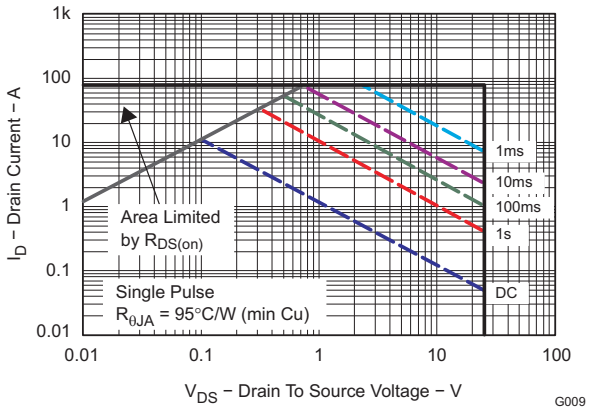

Figure 10. Maximum Safe Operating Area

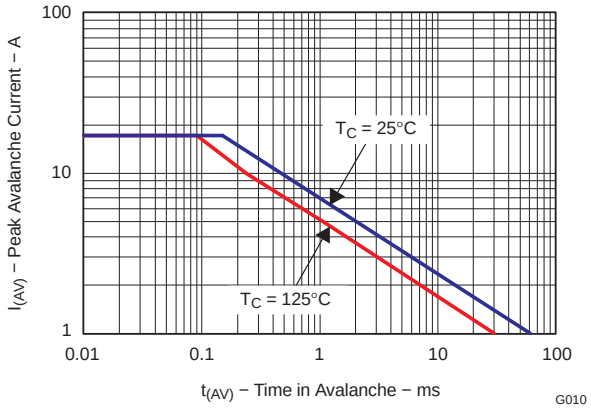

Figure 11. Single Pulse Unclamped Inductive Switching

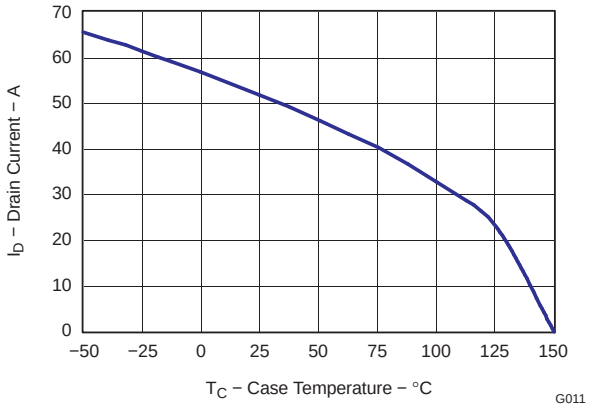

Figure 12. Maximum Drain Current vs. Temperature

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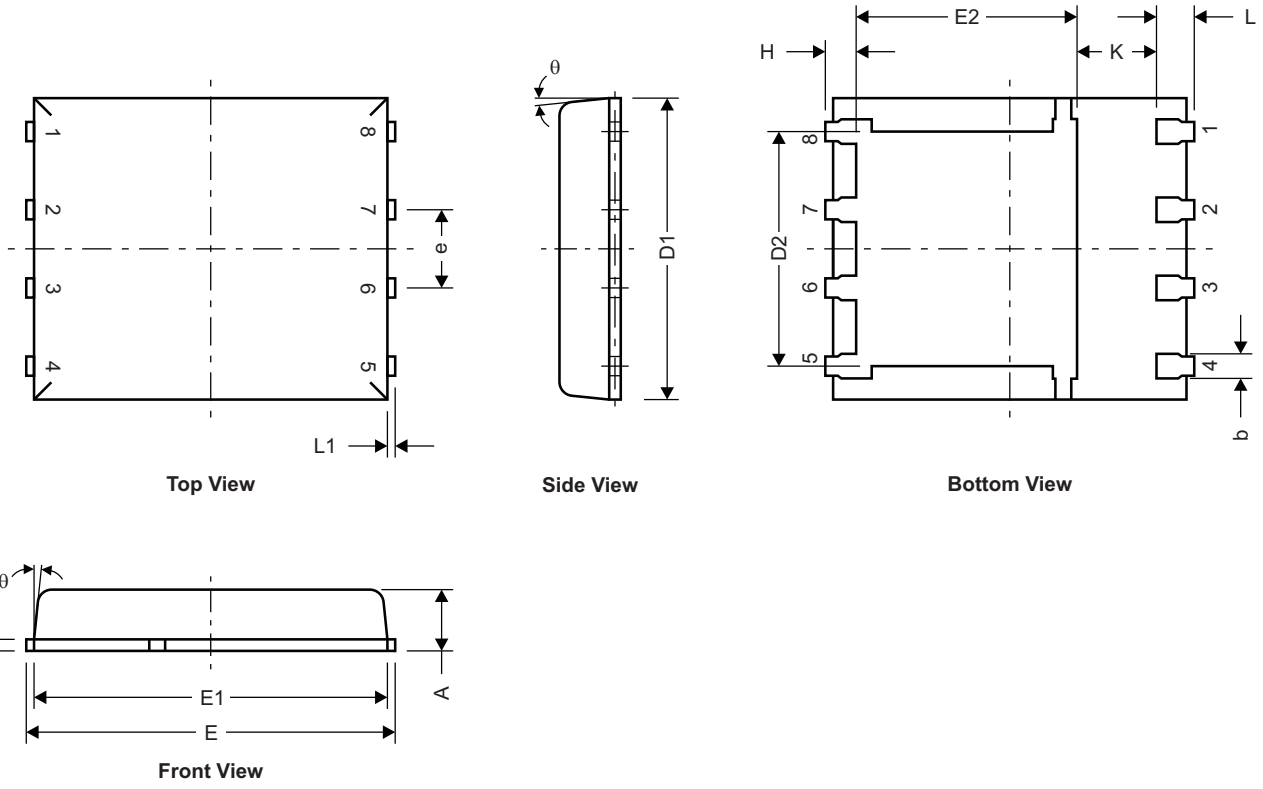
MECHANICAL DATA

Q5A Package Dimensions



M0135-01

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
c	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e		1.27 BSC	
H	0.41	0.51	0.61
K	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°		12°

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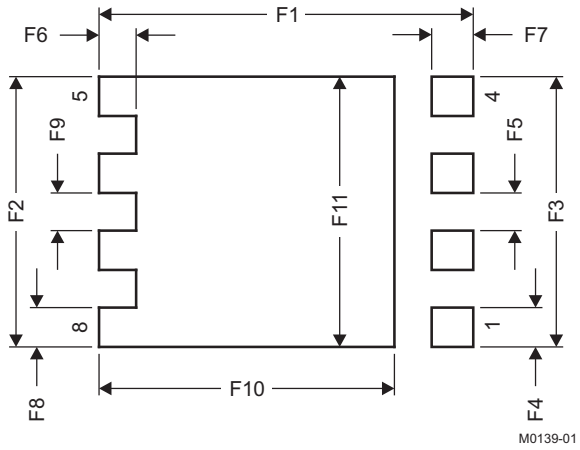
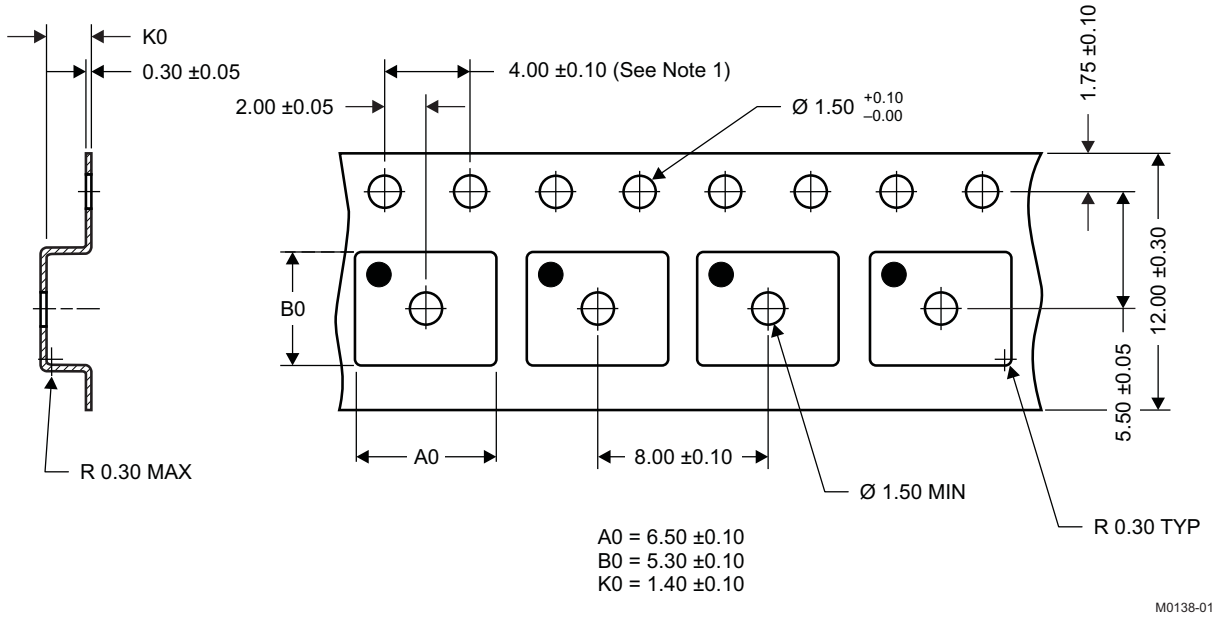
Figure 13. Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

Q5A Tape and Reel Information



Notes:

1. 10 sprocket hole pitch cumulative tolerance ±0.2
2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
3. Material:black static dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified)
5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
6. MSL1 260°C (IR and Convection) PbF Reflow Compatible

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REVISION HISTORY

Changes from Original (August 2009) to Revision A	Page
• Deleted the Package Marking Information section	7

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD16412Q5A	ACTIVE	VSONP	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD16412	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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